

SOT-89 Plastic-Encapsulate Transistors

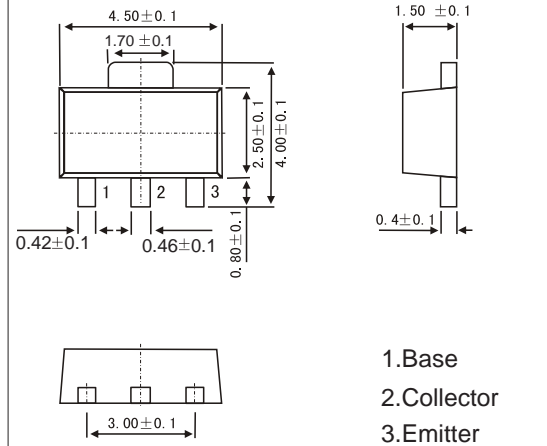
Features

- Low VCE(sat)
- Compliments to 2SD1664
- PNP Transistors

MECHANICAL DATA

- Case style: SOT-89 molded plastic
- Mounting position: any

SOT-89



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-40	V
Collector-Emitter Voltage	V _{CEO}	-32	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current (DC)	I _c	-1	A
Single pulse, P _w =100ms		-2	A
Collector Power Dissipation	P _c *	0.5	W
Junction temperature	T _j	150	°C
Storage temperature Range	T _{stg}	-55 to +150	°C

PACKAGE INFORMATION

Device	Package	Shipping
2SB1132	SOT-89	3000/Tape&Reel

* When mounted on a 40x40x0.7mm ceramic board.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _c = -50μA, I _E =0	-40			V
Collector- emitter breakdown voltage	V _{CEO}	I _c = -1 mA, I _B =0	-32			
Emitter - base breakdown voltage	V _{EB0}	I _E = -50 μ A, I _C =0	-5			
Collector-base cut-off current	I _{CB0}	V _{CB} = -20 V, I _E =0			-0.5	uA
Emitter cut-off current	I _{EB0}	V _{EB} = -4V, I _C =0			-0.5	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500 mA, I _B =-50mA		-0.2	-0.5	V
DC current gain	h _{FE}	V _{CE} = -3V, I _C = -0.1A	82		390	
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0mA, f=1MHz		20	30	pF
Transition frequency	f _T	V _{CE} = -5V, I _E = 50mA, f=30MHz		150		MHz

hFE Classification

Type	2SB1132-P	2SB1132-Q	2SB1132-R
Range	82-180	120-270	180-390
Marking	BAP*	BAQ*	BAR*

RATINGS AND CHARACTERISTIC CURVES

■ Typical Characteristics

